

PATENT

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CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

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Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patents or patent applications identified to Renesas Technology Corp. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong Taek Kong
Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: July 7, 2008

APPENDIX A

| Application No. | Patent No. | Filing Date | Title of Patent |
|-----------------|------------|-------------------|---|
| 08/841612 | 5,870,218 | 04/30/1997 | Non-volatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 09/096457 | 5,982,667 | 06/11/1998 | Non-volatile Semiconductor Memory Device For Storing Multivalued Information By Controlling Erase And Plural Write States of Each Memory Cell |
| 09/339960 | 6,181,603 | 06/25/1999 | Non-volatile Semiconductor Memory Device Having Plural Memory Cells Which Store Multi-Value Information |
| 09/715106 | 6,396,736 | 11/20/2000 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 10/154853 | 6,771,537 | 05/28/2002 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 10/832311 | 7,031,187 | April 27, 2004 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 11/332206 | 7,245,532 | January 17, 2006 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 11/595880 | | November 13, 2006 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |

APPENDIX A

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| 12/117918 | | May 9, 2008 | Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information |
| 07/704739 | 5,300,802 | May 20, 1991 | Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements |
| 08/179960 | 5,407,853 | January 11, 1994 | Method of Making Semiconductor Integrated Circuit Device Having Single-Element Type Non-Volatile Memory Elements |
| 08/422941 | 5,656,839 | April 17, 1995 | Semiconductor Integrated Circuit Device Having Single-Element Type Nonvolatile Memory Elements |
| 08/422940 | 5,629,541 | April 17, 1995 | Semiconductor Memory Device Constituted by Single Transistor Type Non-volatile Cells and Facilitated for Both Electrical Erasing and Writing of Data |
| 08/451268 | 5,656,522 | May 30, 1995 | Method of Manufacturing a Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements |
| 08/885184 | 5,904,518 | June 30, 1997 | Method of Manufacturing a Semiconductor IC Device Having Single Transistor Type Nonvolatile Memory Cells |
| 09/282204 | 6,255,690 | March 31, 1999 | Non-volatile Semiconductor Memory Device |
| 09/873451 | 6,451,643 | June 5, 2001 | Method of Manufacturing a Semiconductor Device Having Non-volatile Memory Cell Portion with |

APPENDIX A

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| 10/164626 | 6,777,282 | | June 10, 2002 | Single Transistor Type Memory Cells and Peripheral Portion with MISFETs |
| 10/819205 | 6,960,501 | | April 7, 2004 | Method of Manufacturing a Semiconductor Memory Device Having a Memory Cell Portion Including MISFETs With a Floating Gate and a Peripheral Circuit Portion With MISFETs |
| 11/220723 | 7,071,050 | | September 8, 2005 | Method of Manufacturing a Semiconductor Memory Device Having a Non-volatile Memory Cell Portion with Single MISFET Transistor Type Memory Cells and a Peripheral Circuit Portion with MISFETs |
| 11/393774 | | | March 31, 2006 | Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements |
| 08/913338 | 5,978,941 | | September 11, 1997 | Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements |
| 09/432389 | 6,223,311 | | November 2, 1999 | Semiconductor Memory Device Having Deterioration Determining Function |
| 09/794073 | 6,694,460 | | February 28, 2001 | Semiconductor Memory Device Having Deterioration Determining Function |

APPENDIX A

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| 07/517386 | 5,079,603 | April 30, 1990 | Semiconductor Memory Device |
| 07/765065 | 5,189,497 | September 24, 1991 | Semiconductor Memory Device |
| 07/992473 | 5,340,760 | December 15, 1992 | Method of Manufacturing EEPROM Memory Device |
| 08/260229 | 5,472,891 | June 14, 1994 | Method of Manufacturing a Semiconductor Device |
| 08/419232 | 5,604,142 | April 10, 1995 | Method of Making an EPROM With Peripheral Transistor |
| 11/082992 | 7,242,611 | March 18, 2005 | Nonvolatile Semiconductor Memory Device for Writing Multivalued Data |
| 11/819015 | | June 25, 2007 | Nonvolatile Semiconductor Memory Device for Writing Multivalued Data |
| 11/819016 | | June 25, 2007 | Non-volatile Semiconductor Memory Device for Writing Multivalued Data |
| 09/620719 | 6,496,409 | July 20, 2000 | Variable Capacity Semiconductor Memory Device |
| 08/203303 | 5,422,856 | March 1, 1994 | Non-volatile Memory Programming at Arbitrary Timing Based on Current Requirements |
| 10/700592 | 7,068,541 | November 5, 2003 | Nonvolatile Memory and Method of Erasing for Nonvolatile Memory |
| 11/284949 | 7,072,224 | November 23, 2005 | Nonvolatile Memory and Method of Erasing for Nonvolatile Memory |